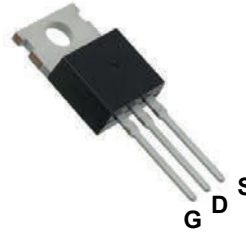
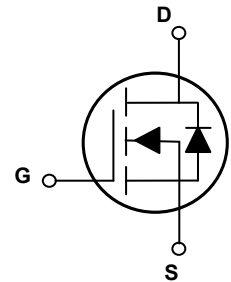


Main Product Characteristics

$V_{(BR)DSS}$	150V
$R_{DS(ON)}$	52m Ω (Typ.)
I_D	20A



TO-220



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFH68015 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current, @ Steady-State (T _C =25°C) ¹	I _D	20	A
Continuous Drain Current, @ Steady-State (T _C =100°C)		14	A
Pulsed Drain Current ²	I _{DM}	80	A
Power Dissipation	P _D	75	W
Linear Derating Factor		0.6	W/°C
Single Pulse Avalanche Energy ³	E _{AS}	25	mJ
Junction-to-Case	R _{θJC}	1.6	°C/W
Junction-to-Ambient (PCB Mounted, Steady-State) ⁴	R _{θJA}	50	°C/W
Operating Junction and Storage Temperature Range	T _J /T _{STG}	-55 to +150	°C

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	150	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$	-	-	1	μA
		$T_J=125^\circ\text{C}$	-	-	50	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS}=20V$	-	-	100	nA
		$V_{GS}=-20V$	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$	-	52	68	m Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.1	3	3.9	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=75V, f=1\text{MHz}$	-	518	-	pF
Output Capacitance	C_{oss}		-	76	-	
Reverse Transfer Capacitance	C_{rss}		-	3.3	-	
Total Gate Charge	Q_g	$I_D=5A, V_{DS}=75V, V_{GS}=10V$	-	9.1	-	nC
Gate-to-Source Charge	Q_{gs}		-	3.5	-	
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	1.8	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=30V, I_D=5A, R_{GEN}=6\Omega$	-	7.3	-	nS
Rise Time	t_r		-	24	-	
Turn-Off Delay Time	$t_{d(off)}$		-	14	-	
Fall Time	t_f		-	22	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	2.5	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	20	A
Pulsed Source Current (Body Diode)	I_{SM}		-	-	80	A
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V$	-	1	1.2	V
Reverse Recovery Time	T_{rr}	$I_S=5A, V_{GS}=0V, di/dt=100A/\mu s$	-	53	-	μs
Reverse Recovery Charge	Q_{rr}		-	0.11	-	nC

Note:

1. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. $L=0.5\text{mH}, R_G=25\Omega, V_{DD}=50V, I_{AS}=10A, T_J=25^\circ\text{C}$.
4. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Typical Electrical and Thermal Characteristic Curves

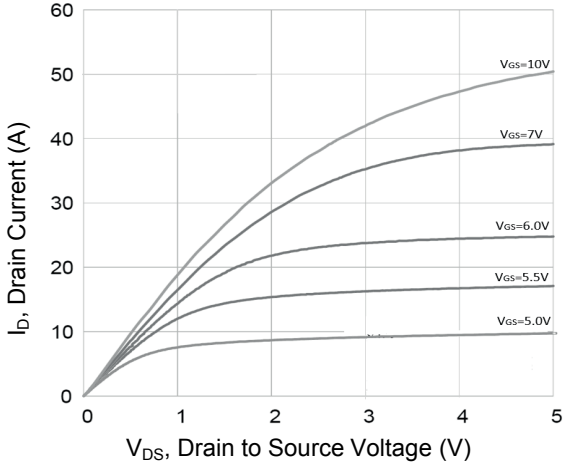


Figure 1. Typical Output Characteristics

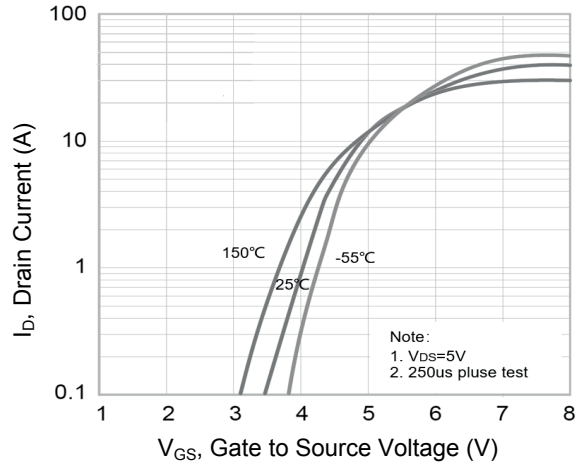


Figure 2. Transfer Characteristics

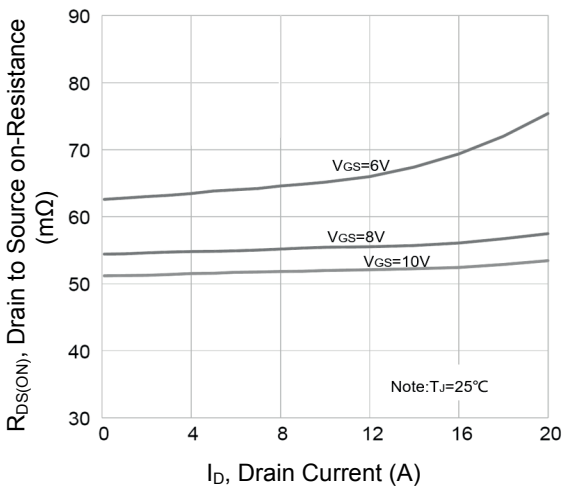


Figure 3. $R_{DS(ON)}$ vs. Drain Current

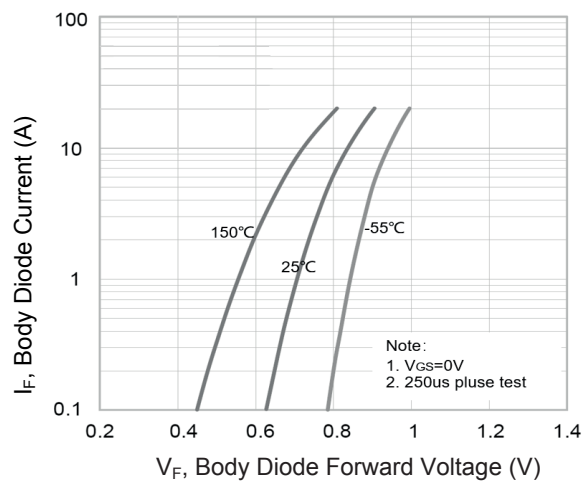


Figure 4. Body Diode Characteristics

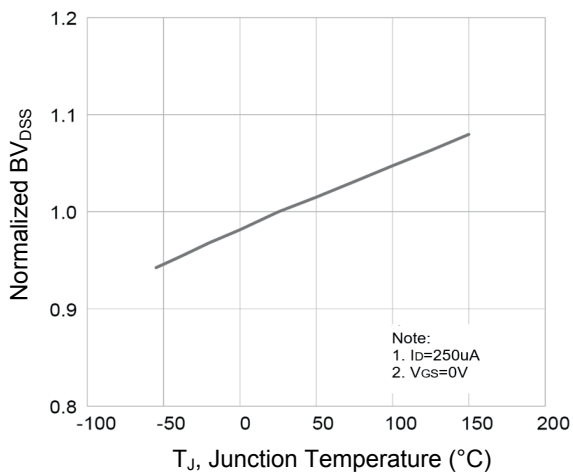


Figure 5. Normalized BV_{DSS} vs. T_J

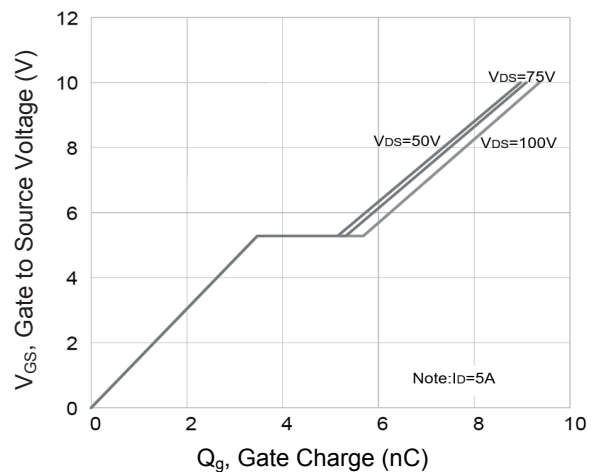


Figure 6. Gate Charge

Typical Electrical and Thermal Characteristic Curves

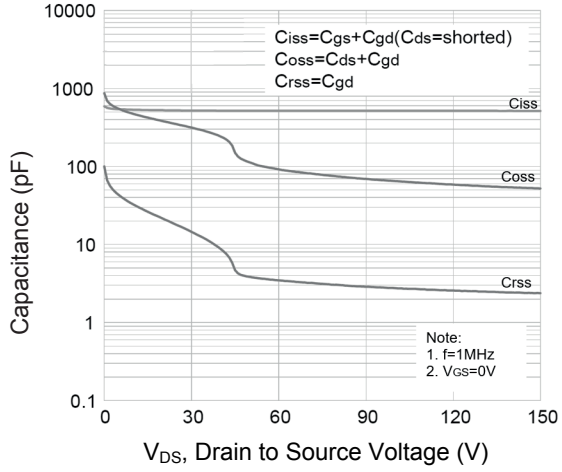


Figure 7. Capacitance Characteristics

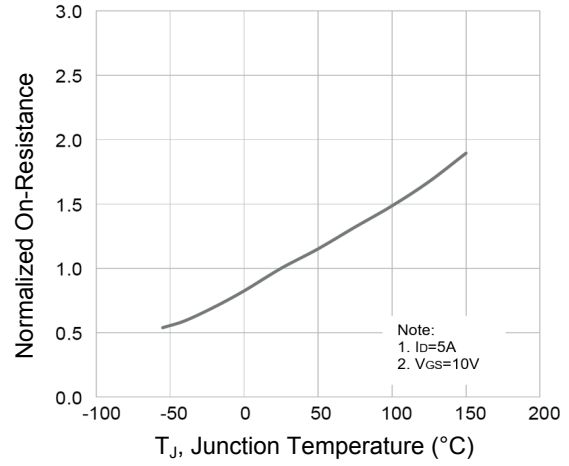
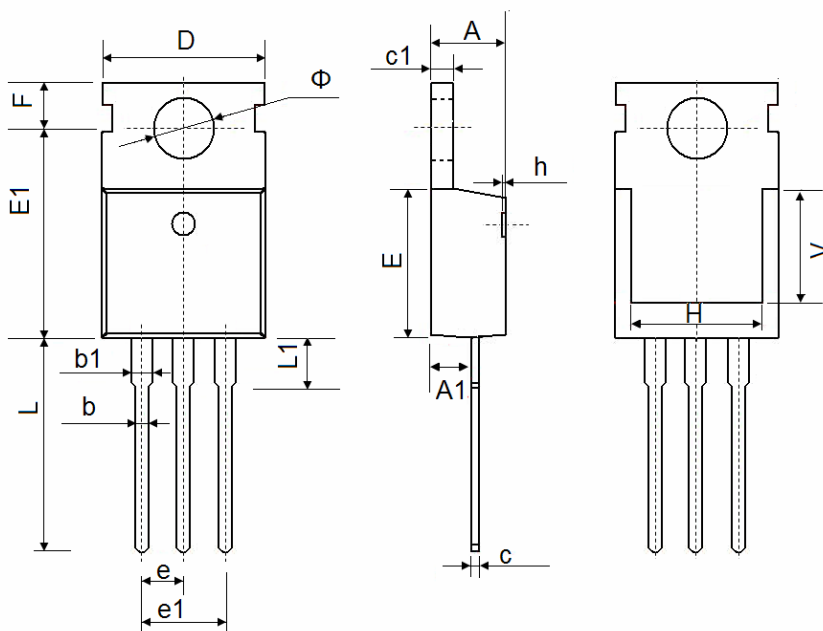


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

Package Outline Dimensions (TO-220)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
φ	3.400	3.800	0.134	0.150

Order Information

Device	Package	Marking	Carrier	Quantity
GSFH68015	TO-220	H68015	Tube	50 pcs / Tube

For more information, please contact us at: inquiry@goodarksemi.com